

09/926454

**PATENT APPLICATION**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Syouji HIGASHIDA et al.

New U.S. National Phase of PCT/JP01/01672

Filed: November 6, 2001

Attorney Dkt. No.: 107400-00044

For: SEMICONDUCTOR DEVICE

*3/4/9*  
*1-29-02*

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

November 6, 2001

Sir:

Prior to initial examination of the application, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend claims 5 and 6 as follows:

5. (Amended) The semiconductor device of claim 1, wherein said p-type layers and said n-type layers are formed so as to have the same width and the same concentration of impurities, in the same conductivity type, respectively.

6. (Amended) The semiconductor device of claim 1, wherein a diffusion region having a difference conductivity type from that of said semiconductor layer is formed on the closest side to said protective diode of said transistor cells arranged, and said source wiring contacted to the most inner layer of said protective diode is contacted to said diffusion region.

*2/1/02*  
*B*